

Quantum Hall effect: the resistivity of a two-dimensional electron gas - a thermodynamic approach

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Abstract. Based on a thermodynamic approach, we have calculated the resistivity of a 2D electron gas, assumed *dissipationless* in a strong quantum limit. Standard measurements, with extra current leads, define the resistivity caused by a combination of Peltier and Seebeck effects. The current causes heating(cooling) at the first(second) sample contacts, due to the Peltier effect. The contact temperatures are different. The measured voltage is equal to the Peltier effect-induced thermoemf which is linear in current. As a result, the resistivity is non-zero as $I \rightarrow 0$. The resistivity is a universal function of magnetic field and temperature, expressed in fundamental units h/e^2 . The universal features of magnetotransport data observed in experiment confirm our predictions.

PACS numbers: 72.20.Pa

1. Introduction

Understanding of electronic transport in solids subjected to high magnetic fields was revised profoundly after the discovery of the quantum Hall effect (Klitzing *et al* 1980) for two-dimensional electron gas(2DEG). This phenomenon manifests an extraordinary transport behavior as the temperature approaches zero. The Hall resistivity, ρ_{xy} , is quantized to h/ie^2 with i being either an integer or rational fraction, while the resistivity, ρ_{xx} , vanishes.

The main goal of this paper is to present a thermodynamic approach to the IQHE problem. We address the problem of zero-temperature transport, where all known scattering events are due to impurities and long-range potential. Both cases were considered by Baskin *et al* (1978) and Fogler *et al* (1997) classically, when 2DEG conductivity was found to follow Drude formalism and vanished at a magnetic field exceeding a certain value, dependent on the dominant scattering. Moreover, the exact solution for 2DEG in a strong magnetic field in the presence of impurities was found by Baskin *et al* (1978). For an impurity concentration per unit area, $\mathcal{N}$, 2DEG conductivity vanishes when $\mathcal{N} < \Gamma = 1/2\pi l_B^2$, where Γ is a zero-width Landau level(LL)

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density of states(DOS), and $l_B = (\hbar c/eB)^{1/2}$ the magnetic length. Following the above scenario, we further investigate the extreme quantum limit, when 2DEG is considered *dissipationless*, and both the conductivity and resistivity tensors are off-diagonal. The thermodynamics of reversible processes are known to be valid (Obraztsov 1964) in such a case. Our support of this idea is confirmed by thermopower measurements data (Obloh *et al* 1984), found to agree with theoretical predictions for dissipationless 2DEG.

The crucial point of this paper is that an extraneous resistivity can, nevertheless, arise from combined Peltier and Seebeck thermoelectric effects (Kirby and Laubitz 1973, Cheremisin 2001). The current leads to heating(cooling) at the first(second) sample contacts, owing to the Peltier effect. The contact temperatures are different, and the temperature gradient is linear in current. The voltage drop is equal to the thermoemf induced by the Peltier effect. As a result, the resistivity associated with the above voltage is nonzero. We argue that this value may be identified as the 2DEG resistivity proper. We compared our results with experimental data. In fact, the possible undesirable influence of thermoemf on QHE measurements was discussed among experimentalists (Shahar, 2002).

2. Analytical approach

According to conventional thermodynamics, the chemical potential, μ , for system conductors+2DEG(see figure 1, inset) is constant at equilibrium. Moreover, μ remains constant under minor current induced fluctuations from the equilibrium. We conclude that 2DEG is non-isolated. We argue that an external reservoir of electrons, if it exists, could provide the pinning of the 2DEG chemical potential. Baraff and Tsui(1980) and Konstantinov *et al* (1983) suggested that the remote ionized donors(surface states in Si-MOS) may serve as such a reservoir. If we suppose that μ is fixed, it can be shown that the 2DEG density, N , changes with the magnetic field. Indeed, at $T \rightarrow 0$, $N = i\Gamma$ electrons are required in order to occupy i levels. Hence, the Hall conductivity is given by $\sigma_{yx} = Nec/B = ie^2/h$. The reservoir must furnish the opportunity for the variation of N over sufficiently wide limits in order to achieve observable σ_{yx} -plateaux. Unfortunately, this scenario ceased (Klitzing *et al* 1984), because of insufficient strength of the reservoir in both models. In contrast, the experiments (Nizhankovskii *et al* 1986) support the reservoir conception and point to an oscillatory dependence of electron density on magnetic field. We claim that the 3D electrons of the metal leads can play a role in such a reservoir. Indeed, in a strong magnetic field, when only a few LLs are filled, the absolute change in N at a fixed μ is of the order of density, $N_0 = \frac{m\mu}{\pi\hbar^2}$, of strongly degenerated 2DEG at $B = 0$. Hence, the number of 3D reservoir electrons changes. The relative variation of the chemical potential of 3D electrons is given by $\delta\mu/\mu = \frac{2}{3}N_0lw/N_{3D}$, where l, w are the length and width of 2DEG, and $N_{3D} \approx 10^{23}$ is the total number of 3D electrons. For a typical sample ($1 \times 3 \text{ mm}^2$, $N_0 = 10^{11} \text{ cm}^{-2}$) we have $\delta\mu/\mu \approx 10^{-15}$. Evidence shows that 2D chemical potential is fixed under such conditions, providing the expected quantization accuracy.

Let us consider a 2DEG in the x-y plane (figure 1, inset), subjected to a magnetic field $B = B_z$. The 2DEG structure is arbitrary, the electrons are supposed to occupy the first size-quantization sub-band. For simplicity, we disregard spin effects, the 2D electron energy spectrum being $\epsilon_n = \hbar\omega_c(n + 1/2)$, where $n = 0, 1, \dots$ is the LL number, and $\omega_c = eB/mc$ the cyclotron frequency. Then, we assume no further LL broadening within the extreme quantum limit $\hbar\omega_c \gg kT$. A Hall-bar geometry sample is connected to the current source by means of two identical leads. The contacts are assumed to be ohmic. The voltage is measured between the open ends ("e" and "d"), kept at the temperature of the external thermal reservoir. The sample is placed in a chamber with a mean temperature T_0 . Including the temperature gradient term, the macroscopic current, $\mathbf{j}$, and the energy flux, $\mathbf{q}$, densities are given by

$$\mathbf{j} = \hat{\sigma}(\mathbf{E} - \alpha \nabla T), \quad \mathbf{q} = (\alpha T - \zeta/e)\mathbf{j} - \hat{\kappa} \nabla T. \quad (1)$$

Here, $\mathbf{E} = \nabla\zeta/e$ is the electric field, $\zeta = \mu - e\varphi$ the electrochemical potential, and α the thermopower. The conductivity, $\hat{\sigma}$, and resistivity, $\hat{\rho}$, tensors are assumed to be off-diagonal, therefore $\sigma_{yx} = 1/\rho_{yx}$. Then, $\hat{\kappa} = LT\hat{\sigma}$ is the electron-related thermal conductivity, and $L = \frac{\pi^2 k^2}{3e^2}$ the Lorentz number. Note that (1) is valid for a confined-topology sample, for which the diamagnetic surface currents (Obratsov 1964) are accounted. Both Einstein and Onsager relationships are satisfied. In fact, (1) represents the current and energy dissipationless fluxes caused by electron drift in crossed fields (for 3D case, see Zyryanov 1964). Using (1), we obtain

$$j = j_x = \sigma_{xy}E_y, \quad j_y = \sigma_{yx}(E_x - \alpha \nabla_x T) = 0. \quad (2)$$

The current represents the flux of electrons in crossed fields with a drift velocity $v_{dr} = cE_y/B$, where E_y is the Hall electric field. The transverse electron flow caused by the longitudinal electric field E_x is compensated by that associated with the downstream temperature gradient.

We can now determine the temperature gradient caused by the Peltier effect. Recall that Peltier heat is generated by a current crossing the contact between two different conductors. At that contact (for example "a" in figure 1, inset), the temperature, T_a , electrochemical potential ζ , normal components of the total current, I , and the total energy flux are continuous. There exists a difference $\Delta\alpha = \alpha_m - \alpha$ between the thermopowers of the metal and 2DEG, respectively. At $\Delta\alpha > 0$, the charge crossing the contact "a" gains an energy $e\Delta\alpha T_a$. Consequently, $Q_a = I\Delta\alpha T_a$ is the amount of Peltier heat evolved per unit time in the contact "a". For $\Delta\alpha > 0$ and current flow direction shown in figure 1, the contact "a" is heated and the contact "b" is cooled. The contacts are at different temperatures, and $\Delta T = T_a - T_b > 0$. At small currents, the temperature gradient is small and $T_{a,b} \approx T_0$. In this case, α can be assumed to be constant, and, hence, we disregard Thomson heating ($\sim IT\nabla\alpha$) of 2DEG. As will be shown, the sample cooling caused by heat leak via the leads and 3D substrate is negligible. Hence, we consider a 2DEG under adiabatic cooling conditions, when the amount of the Peltier heat evolved at the contact "a" is equal to that absorbed at the contact "b".

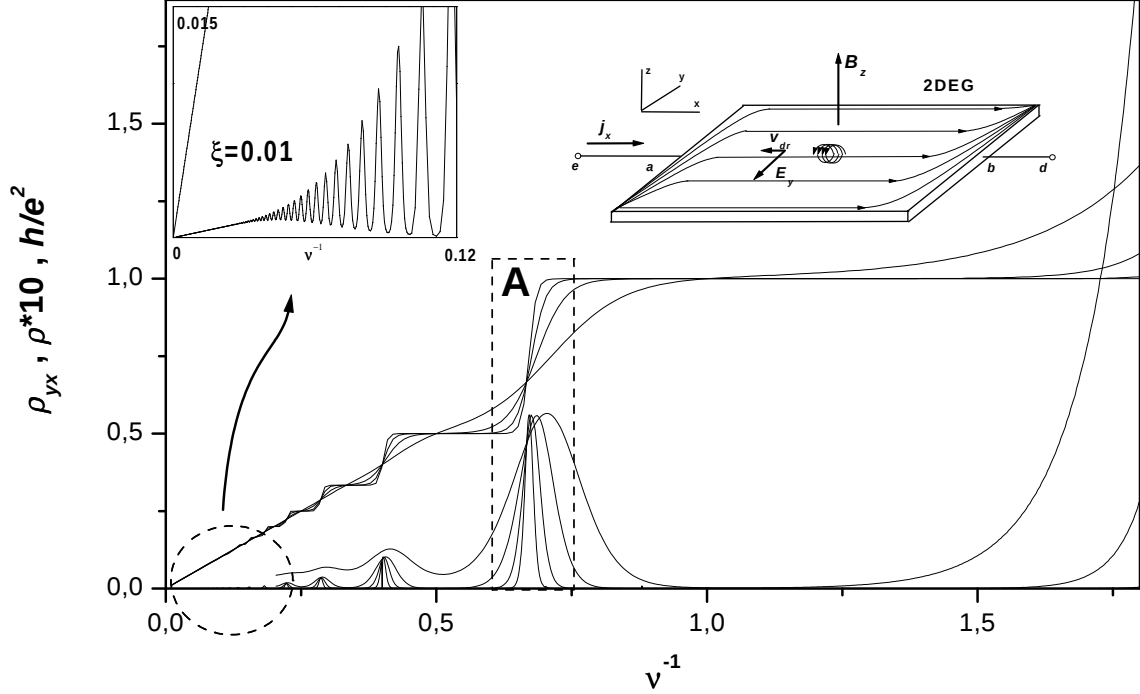


Figure 1. Magnetic field dependence of ρ_{yx} and ρ (scaled by a factor of 10) given by (3) for $\xi = 0.01, 0.02, 0.04, 0.08$. The enlarged plot of data depicted in section A is represented in figure 2. Insets: (left) Low-field dependence of resistivities given by (3,4); (right) QHE experimental setup

The energy flux is continuous at each contact, thus $\kappa_{yx} \nabla_x T|_{a,b} = -j \Delta \alpha T_{a,b}$. Here, we take into account that the current is known to enter and leave the sample at two diagonally opposite corners (figure 1, inset). The temperature gradient is given by $\nabla_x T = -j \Delta \alpha \rho_{yx}$, thus being linear in current. The voltage drop, U , measured between the ends "e" and "d" is found to be $U = \int E_x dx = \int \alpha dT = \Delta \alpha (T_a - T_b)$. Ignoring conductor resistances, both the Hall and Peltier-effect-induced resistivities yield

$$\rho = U/jl = s \rho_{yx}, \quad \rho_{yx}^{-1} = N e c / B = e^2 / h \sum_n f(\varepsilon_n), \quad (3)$$

where $s = \frac{\alpha^2}{L}$, $N = -\left(\frac{\partial \Omega}{\partial \mu}\right)_T$ is the 2D density, $\Omega = -kT \Gamma \sum_n \ln \left[1 + \exp\left(\frac{\mu - \varepsilon_n}{kT}\right)\right]$ the thermodynamic potential, and $f(\epsilon)$ the Fermi function. We take into account in (3) that for actual case of metal leads $\Delta \alpha \simeq -\alpha$. Note that the dissipated power is positive, since $\rho j^2 > 0$. (3) can also then be applied to four-probe Hall-bar measurements and to the 2DHG case.

Recall that in the strong quantum limit, 2D thermopower is a universal quantity

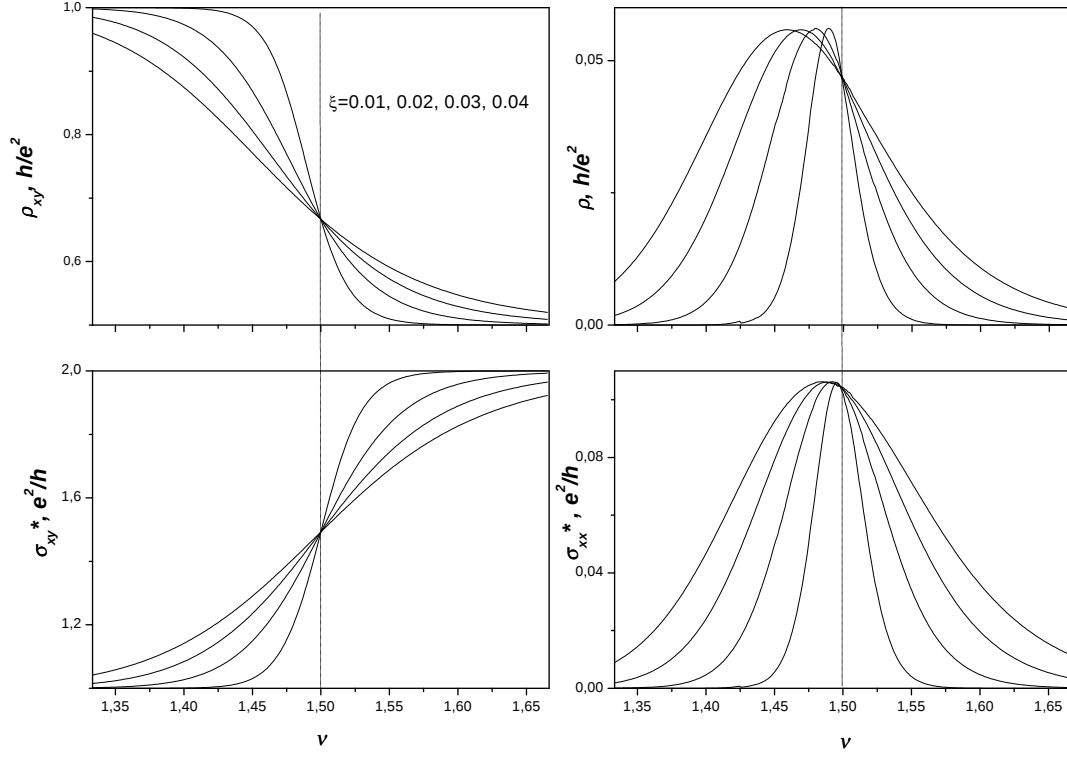


Figure 2. (top) The enlarged plot of ρ_{yx}, ρ data denoted by section A in figure 1 and the related conductivities (bottom) $\sigma_{yx}^*, \sigma_{xx}^*$ given by (5) in the vicinity of half-filled LL $\nu_{cr} = 3/2$

(Girvin and Jonson 1982), proportional to the entropy per single electron: $\alpha = -\frac{S}{eN}$, where $S = -\left(\frac{\partial \Omega}{\partial T}\right)_\mu$ is the 2DEG entropy. It can be demonstrated that S, N, α are universal functions of the reduced temperature $\xi = kT/\mu$ and the magnetic field $\hbar\omega_c/\mu = \nu^{-1}$, where ν is the filling factor. Actually, ν corresponds to the conventional filling factor, when spin effects are taken into account. Using Lifshitz-Kosevich conventional formalism, asymptotic formulae can easily be derived for N, S , and hence for ρ_{yx}, ρ , valid within low-temperature and magnetic field limits $\nu^{-1}, \xi < 1$:

$$N = N_T + \pi\xi N_0 \sum_{k=1}^{\infty} \frac{(-1)^k \sin(2\pi k\nu)}{\sinh(r_k)}, \quad S = S_0 - \pi^2 \xi k N_0 \sum_{k=1}^{\infty} (-1)^k \Phi(r_k) \cos(2\pi k\nu), \quad (4)$$

where $N_T = \frac{N_0}{2} \xi F_0(1/\xi)$ is the density, $S_0 = k \frac{N_0}{2} \frac{d}{d\xi} [\xi^2 F_1(1/\xi)]$ the entropy at $B = 0$. Then, $\Phi(z) = \frac{1-z \coth(z)}{z \sinh(z)}$, $F_n(y)$ is the Fermi integral, $r_k = 2\pi^2 \xi \nu k$ the dimensionless parameter.

According to the above reasoning, the resistivities given by (3) are universal functions (see figure 1) of ξ, ν expressed in fundamental units $\frac{h}{e^2}$. Indeed, $\alpha \sim k/e$,

Table 1. Critical resistivity within 2-1 and 1-0 QH transition

2D gas	$n(10^{10}cm^{-2})$	$\mu(10^4 \frac{cm^2}{Vs})$	$\nu_{cr}, \rho^{cr}(2-1)$	$\nu_{cr}, \rho^{cr}(1-0)$	paper
n-InP	33.7	3.5	1.61/0.07		Wei,1985
— . —	33	3.5	1.53/0.19		Wei,1988
— . —	20	1.6	1.52/0.13		Hwang,1993
— . —	4	9.4	0.17	0.88	Pan,1997
— . —	3	3		0.56/1.18	Shahar,1998
n-GaAs	3.5-22.6	1.2-5.2		0.55-0.67/0.77-1.32	Shahar,1995
— . —	22.7	1.1	1.52/0.16	0.62/1.18	Shahar,1997
— . —	20	80	1.60/0.11	0.54/0.88	Wong,1997
p-SiC	34	1.3	1.60/0.15		Coleridge,1999
— . —	8.7			0.87/2.2	Hilke,1997

and, therefore $\rho \sim \rho_{yx}$. Within classical magnetic field limits (figure 1, inset), we obtain $\rho_{yx} = \frac{h}{\nu e^2}$. Then, in a strong magnetic field when the chemical potential lies between the two LLs, ρ_{yx} is quantized to $\frac{h}{\nu e^2}$, while ρ is thermally activated with activation energy of the order of the magnetic energy. Using (3) we find out the activation energy, $\Delta E = \frac{d \ln \rho}{d \xi - 1}$, for ρ close to filling factor $\nu = 2$. The resonance-like curve(see figure 3,inset) is confined by two lines which define the shift of the two neighboring LLs with respect to Fermi energy. At $\nu = 2$, the chemical potential lies in the middle of the two proximate LLs, therefore the activation energy has a maximum $\Delta E = 0.415 \sim 1/\nu = 0.5$ close to an experimental (Wei *et al* 1985) value of 0.42. With the help of (3), at $\xi \ll 1$ for integer fillings $\nu = 1, 2, \dots$ the explicit formulae $\rho = \frac{h}{e^2} \frac{3}{\pi^2 \nu^3} \left(2 + \frac{1}{\nu \xi}\right)^2 \exp\left(-\frac{1}{\nu \xi}\right)$ allows us to find out the above value of the activation energy. The problem whether the conventional localization or present mechanism dominate ρ -minima will be examined elsewhere.

At half-filled LLs ($\nu_{cr} = 1/2, 3/2, \dots$) the α , ρ_{yx} and ρ approach the universal values $\alpha_{cr} = -\frac{k \ln 2}{e \nu_{cr}}$, $\rho_{yx}^{cr} = \frac{h}{e^2} \nu_{cr}^{-1}$, and $\rho^{cr} = \rho_{yx}^{cr} \alpha_{cr}^2 / L$, irrespective of temperature, effective mass, etc. It can be demonstrated that, in the vicinity of critical fillings, $\delta \nu = \nu - \nu_{cr}$, the Hall resistivity can be represented as $\rho_{yx} = \rho_{yx}^{cr} (1 - \delta \nu / \nu_0)$ for $\delta \nu / \nu_0 \ll 1$. Then, $\rho = \rho^{cr} (1 - 3 \delta \nu / \nu_0)$, where $\nu_0 = 4 \nu_{cr}^2 \xi$ is the logarithmic slope dependent on sample and temperature. Note that $\nu_0 \nu_{cr}^{-2}$ is independent of the LL number. We argue that the above universal values ρ^{cr} , ρ_{yx}^{cr} can be associated with the "QH transition points" discussed in the press. To confirm this, in figure 2 the detailed dependencies $\rho(\nu)$, $\rho_{yx}(\nu)$ in the vicinity of $\nu_{cr} = 3/2$ are presented. Evidence shows that this set of curves can be collapsed (Shahar *et al* 1997, Coleridge *et al* 1999) into a single curve, since ρ, ρ_{yx} are universal functions of ξ, ν . As an example, at $\nu_{cr} = 1.66$ (see Wei *et al* 1985, spin is accounted) we have $\rho^{cr} = 0.034 \frac{h}{e^2}$, consistent with an experimental value of 0.07. The experimental observations(see Table1) demonstrate a certain range $0.07 - 0.19 \frac{h}{e^2}$ of ρ^{cr} -magnitude, which is higher compared with that in theory. However, for 1-0 QH transition the agreement between theory($\nu_{cr} = 1/2, \rho^{cr} = 1.17 \frac{h}{e^2}$) and experimental results is somewhat better. We stress that "QH transitions" exhibit a certain universality irrespective to sample, 2D density and ~ 100 -fold change in scattering strength(see Table

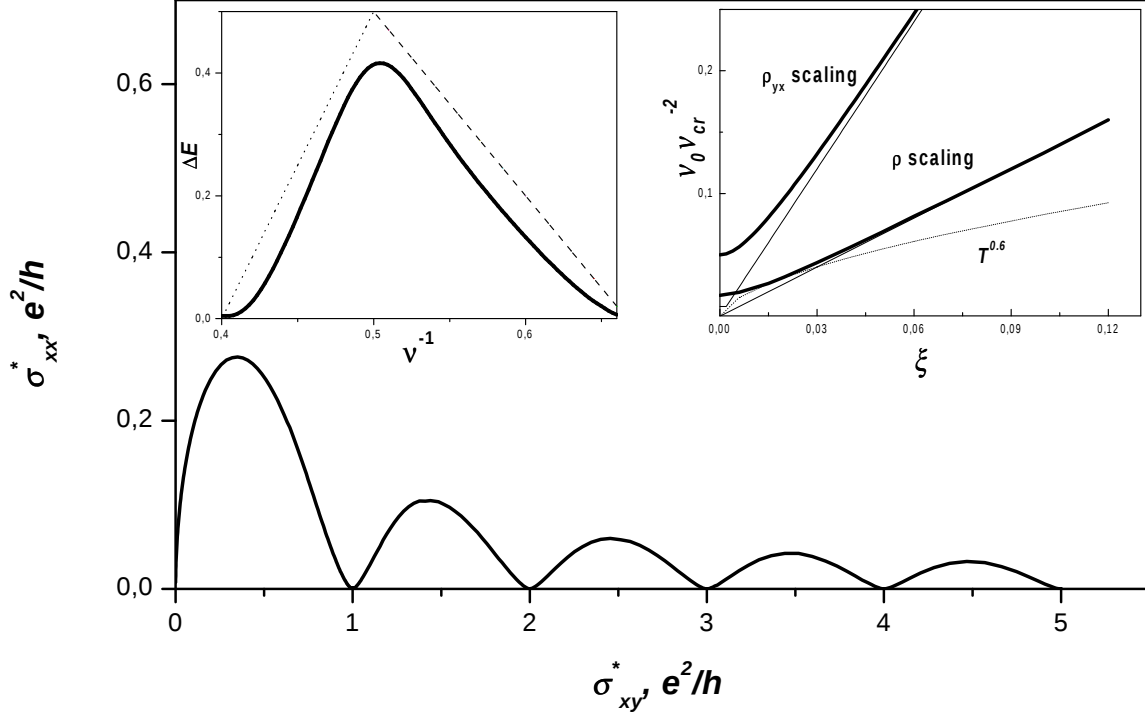


Figure 3. "Semicircle" plot: σ_{xx}^* vs σ_{xy}^* at fixed temperature $\xi = 0.01$. Insets: (left) Activation energy of ρ -minimum in the vicinity $\nu = 2$ at finite temperature $\xi = 0.02$. Dashed(dotted)lines denote the shift of $n=1(2)$ LLs, with respect to Fermi energy; (right) T-scaling of the logarithmic slope $\nu_0 \nu_{cr}^{-2}$ for both the Hall resistivity ρ_{yx} , and ρ at $\nu_{cr} = 3/2$ and fixed LL broadening width $\gamma/\mu = 0.04$. The thin line corresponds to a zero LL width case. The dotted line denotes power-law fit $T^{0.6}$.

1), hence strongly support the dissipation-free 2DEG scenario in question.

It is worthwhile to mention that the existence of T-independent "QH-transition points" is, in fact, the direct consequence of the zero-width LL model in question. Indeed, for half-filled LL we obtained the above results, since $\Omega = -kT \ln 2$, $S = k \Gamma \ln 2$, then $N = \Gamma \nu_{cr}$. This apparent discrepancy with respect to the second law of thermodynamics, namely that $S \neq 0$ at $T = 0$, will be discussed within the realistic model of nonzero LLs width.

It is to be noted that the relationship between the resistivity and conductivity of tensors components has not yet been established experimentally. Within the QH plateaux, the Corbino topology measurements (Dolgoplov *et al* 1991) demonstrate that $\sigma_{yx} = 1/\rho_{yx}$. In practice, both the transverse and the longitudinal conductivities are always derived from the Hall-bar sample resistivity data. Assuming that both the ρ_{yx} , ρ components are those actually measured, we calculate the related conductivities

by means of transformation $(\sigma^*)^\wedge = (\rho^\wedge)^{-1}$ as follows:

$$\sigma_{yx}^* = \sigma_{yx}/(1 + s^2), \quad \sigma_{xx}^* = s\sigma_{yx}^*. \quad (5)$$

Figure 2 represents $\sigma_{xx}^*(\nu), \sigma_{yx}^*(\nu)$ dependencies. These curves can be collapsed into a single plot, as well as ρ, ρ_{yx} (see above) in consistent with experiments (Shahar *et al* 1997, Coleridge *et al* 1999). Using (5), we can derive the relationship $(\sigma_{xx}^*)^2 + (\sigma_{yx}^*)^2 = \sigma_{yx}^* \sigma_{yx}$ between both the $\sigma_{xx}^*, \sigma_{yx}^*$ components. This dependence (figure 3) is similar to that known as the "semicircle" relation.

The known electron-phonon coupling is weak below $\sim 1\text{K}$. Hence, the heat transfer from 2DEG to the mixing chamber could occur through the contacts and the leads connected to them. However, the experiments (Mittal *et al* 1994) at $B = 0$ demonstrate that the 2DEG alone is the dominant thermal resistance. The 2DEG cooling is provided by electron thermal conductivity found to follow Wiedemann-Franz law. Accordingly, our adiabatic cooling approach is applicable. At the same time, remote black body radiation heating is known to play an important role as $T_0 \rightarrow 0$. For example, the electron temperature can differ (Mittal *et al* 1994) from that of the mixing chamber refrigerator (30mK) by as much as 100mK. The extraneous power heating of electrons is caused by black body radiation ($\sim \text{pW}$) from the walls of the vacuum can surrounding the refrigerator. Hence, in ultra low-T experiments, 2DEG is overheated: the electron temperature is higher than that of the bath, i.e. $T > T_0$. Neglecting for a moment 2DEG overheating, we have estimated an established temperature gradient. At $\nu_{cr} = 5/2$, we have $\alpha_{cr} = 0.28k/e$, $\rho_{yx}^{cr} = 2h/5e^2$. For a $1 \times 3\text{mm}^2$ sample and a current $I = 2\text{nA}$, we obtain $\nabla_x T \simeq \alpha_{cr} \rho_{yx}^{cr} I (Lw)^{-1} = 16\text{mK/mm}$. At liquid-helium temperatures, $\Delta T/T_0 = 0.01$, confirming our approach as valid. However, at $\nu \ll 0.5$ our basic assumption of a small temperature gradient is violated since $\alpha \rightarrow \infty$. It is to be noted that at elevated currents, the local temperature $T_a + \nabla_x T \cdot x$ is established in the sample, dependent on the ratio I/w , and differing from T_0 . The thinner the sample and/or the higher the current, the greater the difference from T_0 . As a result, the ρ -peaks width depends on the local temperature. This mechanism appears to play a crucial role in current-polarity dependent QHE breakdown (Komiyama *et al* 1996).

We can now improve our model, assuming a LL broadening. DOS can be represented as the sum of Gaussian peaks $D(\varepsilon) = \frac{\Gamma}{\gamma} \sqrt{\frac{2}{\pi}} \sum_n \exp \left[-2 \left(\frac{\varepsilon - \varepsilon_n}{\gamma} \right)^2 \right]$ with LL width, γ , independent of the magnetic field. Obviously, our previous results remain valid when $kT \gg \gamma$. In the opposite case of low-temperature $kT \ll \gamma$, the LL broadening becomes important and determines a ρ_{yx} -plateau width, ρ -peak width and height. Indeed, at $kT \ll \gamma$, DOS can be considered as constant in the vicinity of the n -th LL. A small deviation of $\Delta = \mu - \varepsilon_n$, in the n -th LL, with respect to chemical potential, results in a $\Gamma \sqrt{\frac{2}{\pi}} \frac{\Delta}{\gamma}$ change in the number of occupied states. For ρ_{yx} -scaling, the logarithmic slope is $\nu_0 = \sqrt{\frac{\pi}{2}} \frac{\nu_{cr}^2 \gamma}{\mu}$, i.e. it is proportional to LL width (see figure 3, inset). Then, at $kT \ll \gamma$ the entropy yields $S_{cr} = \frac{\pi^2}{3} \Gamma \sqrt{\frac{2}{\pi}} \frac{k^2 T}{\gamma}$, and therefore the ρ -peaks height decreases at $T \rightarrow 0$. In contrast, ρ -scaling data obeys the ρ_{yx} -scenario, the logarithmic slope being

$\nu_0/3$. Finally, at $T \rightarrow 0$ the height of the ρ peaks decreases, but their width remains finite.

We must emphasize that the effects related to nonzero LL can be masked because of 2DEG overheating. Indeed, upon bath cooling, the electron temperature would be constant, being controlled by remote black body heat sources. In the case of strong heating, the electron temperature is decoupled with respect to bath ($T > T_0$), and the condition $kT \ll \gamma$ cannot be achieved. As a result, the logarithmic slope $\nu_0(T_0)$ is at first linear, and then saturates below a certain value of heat-dependent temperature. Such a saturation behavior is similar to that discussed above within the nonzero-width LL scenario. It should be noted that, in both cases, one can attribute (see figure 3, inset) the dependence $\nu_0(T_0)$ to the power law T_0^p , where $p \ll 1$. In actual fact, the question as to whether the power law or linear scaling scenario is valid is still the subject of heated debate (Huckestein 1995, Sondhi *et al* 1997). Recent experiments (Shahar *et al* 1998, Coleridge 1999, Balaban *et al* 1998) demonstrate that the linear dependence is preferable, while power law application to restricted portions of data is always possible. Neglecting LL broadening and 2DEG overheating, for InGaAs/InP 2D electron gas (Shahar *et al* 1998) at $N_0 = 3 \cdot 10^{10} \text{cm}^{-2}$ and $\nu_{cr} = 0.58$ (spin is accounted), we obtain $4\nu_{cr}^2 \xi / 3 = 0.065 \cdot T_0 (\text{K})$ for ρ -scaling. This result is consistent with the fit $a \cdot T_0 + b$, where $a = 0.088 \text{K}^{-1}$, $b = 0.053$, as found by Shahar *et al* (1998). We attribute the non-zero logarithmic slope at $T_0 \rightarrow 0$ to an extraneous heating of 2DEG. Indeed, $\rho(\nu)$ -data exhibit (Shahar *et al* 1998) a well-pronounced "QH-transition", indicating the unimportance of LL broadening.

Finally, we address the question of 2DEG self-heating due to finite energy dissipation ρj^2 . By equating the unit area power $\rho(I/w)^2$ dissipated in the sample (Koch *et al* 1991) to that absorbed by phonons (Chow *et al* 1996) $P \sim T^4$, we can determine the electron temperature which can be comparable with the bath temperature T_0 and γ/k . If $T > T_0$, we obtain the power-law fit for a ρ -peak width, as $\Delta B \sim T^p \sim (I/w)^{p/2}$, known for current and sample-width scaling. For $p = 0.68$ (see Koch *et al* 1991), we have $\Delta B \sim w^{-0.34}$, consistent with experimental finding $\Delta B \sim w^{-0.43}$. We argue that simultaneous measurement (Balaban *et al* 1998) of temperature and frequency-dependent linear scaling $\Delta B \sim f, T$ points to 2DEG heating by incoming ($\sim \text{nW}$) ac power.

Up to now only the dc case has been discussed. However, our approach can also be applied to the ac case. As shown by Kirby and Laubitz (1973) and Cheremisin (2001), at $B = 0$ the Peltier effect related resistivity vanishes above a certain frequency, dependent on thermal inertial processes. We recall that, in a quantizing magnetic field, macroscopic current and heat fluxes are known to depend on the magnetism of the conducting electrons (Obraztsov 1964). Actually, Eqs.(1) describe the average current and heat densities for a confined topology sample. We argue that the diamagnetic currents could define the dynamics of thermal processes in 2DEG. For $B = 10 \text{T}$, $m = 0.068 m_0$ we have $\omega_c = 2.8 \cdot 10^{13} \text{Hz}$, $l_B = 70 \text{\AA}$. For a sample size $l \sim 1 \text{mm}$, the transit time of an electron scattered at the sample boundary is $t \sim l(\omega_c l_B)^{-1} = 5 \cdot 10^{-9} \text{s}$. Accordingly, we

can estimate the critical frequency to be $f_0 \sim 1/t = 0.2\text{GHz}$. The smaller the sample, the higher f_0 . At the moment, however, a detailed spectral analysis of ρ is beyond the scope of the present paper.

3. Concluding remarks

In conclusion, the magnetotransport measurements of 2D electron(hole) gas, assumed to be dissipationless in the QH regime, result in a resistivity associated with the Peltier and Seebeck effects combined. This value is probably associated with 2D resistivity proper. The resistivity is a universal function of magnetic field and temperature, expressed in units h/e^2 . The observed "QH transitions" demonstrate a certain universality irrespective to sample, 2D density and ~ 100 -fold change in scattering strength, hence support our dissipationless scenario. Our approach may be useful to eliminate the role of thermoelectric effects within QHE regime.

Acknowledgments

This work was supported by RFBR(grant 03-02-17588) and the LSF(HPRI-CT-2001-00114, Weizmann Institute).

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